

# Replacement Sheet

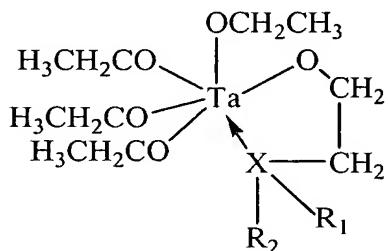
Attorney Docket No. 5649-919



## SEMICONDUCTOR CAPACITORS HAVING TANTALUM OXIDE LAYERS AND METHODS FOR MANUFACTURING THE SAME

### Abstract of the Disclosure

Semiconductor capacitors comprise first electrodes, second electrodes, and tantalum oxide layers positioned between the first electrodes and the second electrodes. The tantalum oxide layers are formed by depositing at least one precursor and ozone gas, the at least one precursor represented by the formula:



wherein X is selected from the group consisting of nitrogen, sulfur, oxygen, and a carbonyl group; and wherein R<sub>1</sub> and R<sub>2</sub> are independently alkyl.

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